DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

High Mobility Heterojunction Complementary Field Effect Transistors and Methods Thereof

the specification of which (check one)		
X is attached hereto.		
was filed on herewith	as	
Application Serial No.	<u> </u>	
and was amended on(if a	applicable)	
I hereby state that I have reviewed and understar above.	nd the contents of the above identified specification, inc	cluding the claims, as amended by any amendment referred to
I acknowledge the duty to disclose information v Section 1.56.	which is material to the patentability of this application	in accordance with Title 37, Code of Federal Regulations,
I hereby claim foreign priority benefits under Tit have also identified below any foreign application	tle 35, United States Code, Section 119 of any foreign a on for patent or inventor's certificate having a filing date	application(s) for patent or inventor's certificate listed below and be before that of the application on which priority is claimed:
Prior Foreign Application(s)		Priority Claimed
		Yes No
Application(s) listed below and, Insofar as the sumanner provided by the first paragraph of Title 3	ubject matter of each of the claims of the application is a 35, United States Code, Section 112, I acknowledge the	United States Provisional Application(s) and Nonprovisional not disclosed in the prior United States application in the duty to disclose information material to the patentability of this ne filing date of the prior application and the national or PCT
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)
further that these statements were made with the	of my own knowledge are true and that all statements m knowledge that willful false statements and the like so de and that willful false statements may jeopardize the v	nade on information and belief are believed to be true; and made are punishable by fine or imprisonment, or both, under validity of the application or any patent issued thereon.
POWER OF ATTORNEY: As a named inventor Patent and Trademark Office connected therewith Number and filing date when received from the	th (list name and registration number). The Attorney of	t(s) to prosecute this application and transact all business in the Record herein is hereby authorized to insert the Application
Redmond, Jr. (Reg. 18,753), Douglas W. C Farrell (Reg. 37,321, Louis P. Herzberg (Re	ameron (Reg. 31,596), Wan Yee Cheung (Reg. 42, eg. 41,500), Derek S. Jennings (Reg. 41,473), Ste	(Reg. 26,914), John E. Hoel (Reg. 26,279), Joseph C. 2,410), Thu Ann Dang (Reg. 41,544), Timothy M. phen C. Kaufman (Reg. 29, 551), Richard M. Ludwin Percello (Reg. 33,206), Robert M. Trepp (Reg. 25,933),
Send Correspondence to: George Sai- 145 Fernwo	Halasz, PhD. (Reg. No. 45,430) od Drive E. Greenwich, RI 02818	Cust. No.: 24299
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DR GEORGE SAI-HALASZ

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DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

High Mobility Heterojunction Complementary Field Effect Transistors and Methods Thereof

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Inventor's Signature	Date
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DECLARATION AND POWER OF ATTORNEY FOR PATENT APPLICATION

High Mobility Heterojunction Complementary Field Effect Transistors and Methods Thereof

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Q. Ouyang and X. Chen Date: October 29, 2003

Group Art Unit:

Serial No.: To be assigned

Examiner: To be assigned

Filed: Herewith

Docket No. YOR920030327US1

For: High Mobility Heterojunction Complementary Field Effect Transistors and

Methods Thereof

Commissioner for Patents Alexandria, VA 22313

APPOINTMENT OF ASSOCIATE POWER OF ATTORNEY

Sir:

Please recognize George Sai-Halasz, Reg. No. 45,430, of 145 Fernwood Dr., E. Greenwich, RI 02818, T: 401-885-8032 as associate attorney, with full power to prosecute, inspect, and transact all business concerning the above-identified application, including the filing of amendments, continuation applications, divisional applications and continuation-in-part applications.

Please send all official correspondence to George Sai-Halasz to the above noted address.

Respectfully submitted,

Reg. No. 42,410

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